

Title (en)

FIELD-EFFECT TRANSISTOR WITH HIGH PACKING DENSITY AND METHOD FOR THE PRODUCTION THEREOF

Title (de)

FELDEFFEKTTRANSISTOR HOHER PACKUNGSDICHTE UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)

TRANSISTOR A EFFET DE CHAMP A DENSITE ELEVEE EN COMPOSANTS ET SON PROCEDE DE PRODUCTION

Publication

**EP 1019965 A1 20000719 (DE)**

Application

**EP 98949904 A 19980814**

Priority

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- DE 19743342 A 19970930

Abstract (en)

[origin: DE19743342A1] The invention relates to a field-effect transistor with a semiconductor body (1) having a main surface and at least one source region (6) and one drain region (7) and fitted with a gate electrode (10) separated from a channel area between the source region (6) and the drain region (7) by an insulator layer (8). The source region (6), the drain region (7) and the channel area in the inventive field-effect transistor are arranged in the walls of the corresponding grooves (3, 4, 5) provided in the semiconductor body (1).

IPC 1-7

**H01L 29/423**; **H01L 29/10**; **H01L 21/336**

IPC 8 full level

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CPC (source: EP KR US)

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